Graphitic contacts in Silicon Carbide and Diamond for dosimetry and radiation detection

Ivan Lopez Paz, Celeste Fleta, Gemma Rius, Joan Marc Rafí, Neil Moffat, Giulio Pellegrini

Proton Therapy Workshop

22 February 2024









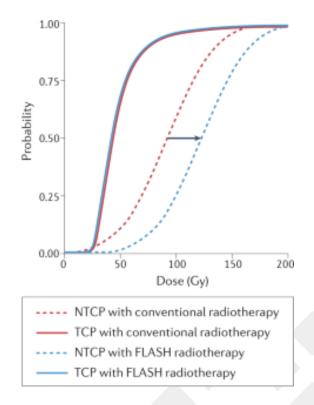
Instrumentation for FLASH

FLASH therapy reduces toxicity in cancer treatments

- 100 kGy/s to 10MGy/s in less than 200 ms
 - <0.03 Gy/s in conventional radiotherapy</p>
- High radiation doses in short times



Nature Reviews Clinical Oncology vol 19, 791–803 (2022)



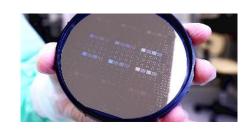




Wide band-gap materials for dosimetry

Properties	Silicon	4H-SiC	CVD Diam.
Band-gap [eV]	1.12	3.23	5.5
e-h pair generation energy [eV]	3.6	7.8	13
Displacement energy threshold [eV]	13-20	22-35	40-50
Thermal conductivity [W/(m K)]	148	370	1000
Atomic number	14		6
Electron sat. velocity (1e17 cm/s)	0.86	3	2
Cost	O(100€)	O(1k€)	





- → Low signals, low background
- → Radiation hard
- → No need for cooling
- \rightarrow Tissue equivalent (Z_{eff} = 7.42)
- → <u>Fast signals</u>
- \rightarrow Expensive...



Sci Rep 7, 44462 (2017)





Graphitic contacts

Typical detectors have **metal** over the active region

- → contribution of secondary interactions
- → can stop low energy ions/light

Here, we try to replace the metal with **graphene/graphite**, a conductive carbon layer

- → less interaction with radiation
- → tissue equivalence

Wide band-gap detectors with carbon contacts





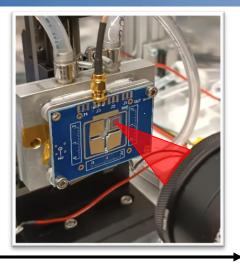
Technologies in this talk

SiC detectors with graphene:

- Study charge formation in 2D
- Dose rate linearity in pre-clinical LINAC
- Characterisaton in X-ray tube

Diamond with graphitic electrodes:

• First prototypes of radiation detectors at CNM







SiC with Graphene contacts





SiC detectors with Graphene contacts

SiC diodes (50um epitaxy) with three geometries fabricated at CNM

No Metal

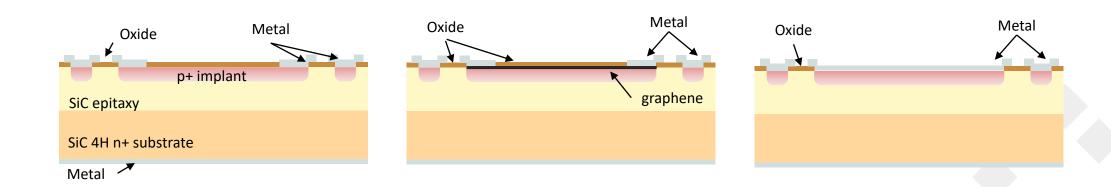
Metal ring around the active region, nothing elsewhere

Graphene

Graphene layer contact over all active region, with metal ring for wirebonding

Metal

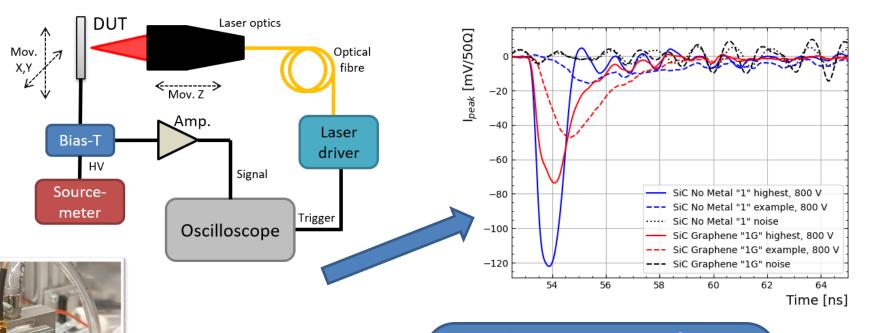
Metallic contact over all active region



Able to study the effect of Graphene in the detectors!







Comparison between signals produced by a "Graphene" and a "No Metal" sample

Note: "Metal" sample cannot be tested under this set-up



 λ =369 nm (UV)

Pulse width: 100 ps

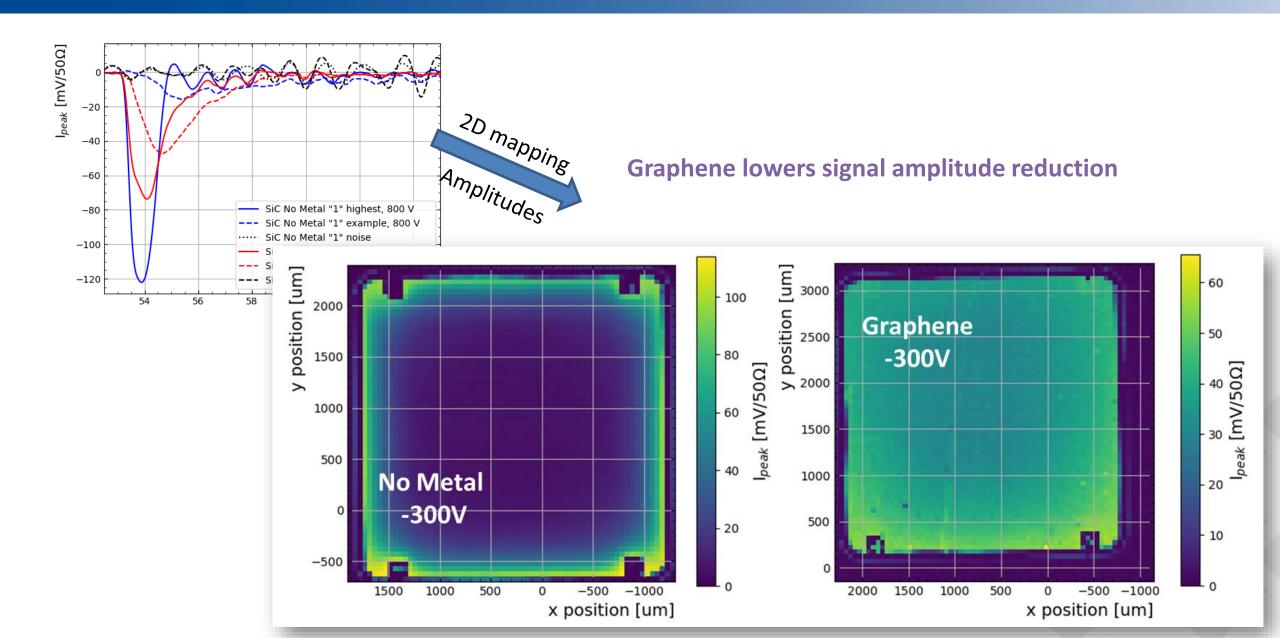
Freq.: 1 kHz rep. rate

Devices: SiC-Graphene

SiC-No Metal

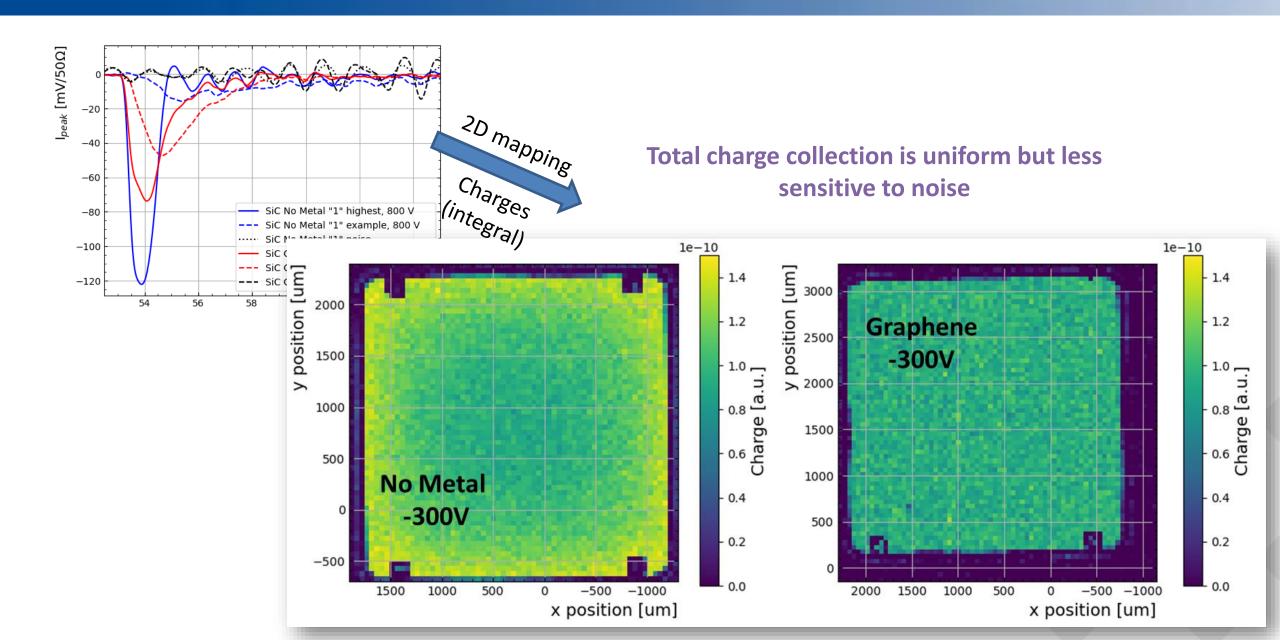
















Graphene, 10x10cm2,

 Q_{fit} = (0.756±0.001) D + (0.029±0.005) nC/30 s

Dose Rate [Gy/min]

 $V_{bias} = 0V$

3

Dosimetry with SiC devices

LINAC

S

[nC/30

Charge |

 $\frac{Q_{data} - Q_{fit}}{Q_{fit}}$ [%]

Op. Voltage: 60MV

Dose rate: 1 - 6 Gy/min

Devices: SiC -- graphene

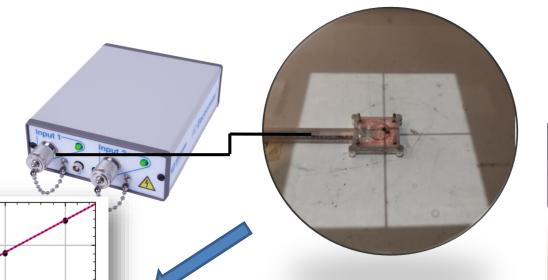
EG-SiC sample

Linear fit $(K \cdot D + I)$ $K = 1.512 \pm 0.002 \text{ nC/Gy}$

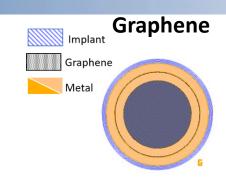
... Exponent fit $(K \cdot D^{\Delta} + I)$ $\Delta = 1.006 \pm 0.006$

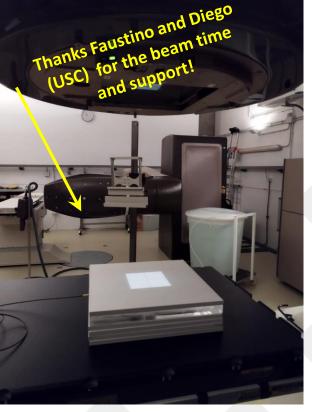
30 sec, 10×10 cm2 field

Readout: Sun Nuclear e-meter



Linac at University of Santiago de Compostela, 8h beam time









Dosimetry with SiC devices

"No Metal" sample looks unstable

"Graphene" and "Metal" samples show a stable and fast behaviour

"Metal" sample is 2x more responsive than "Graphene"

 Multiple scattering due to heavy metals (Au and Ti) on active region Tungsten anode X-ray tube

Op. Voltage: 60kV

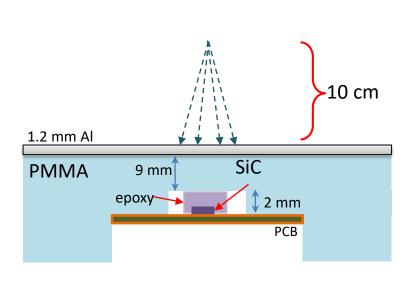
Beam current: 60-120 uA

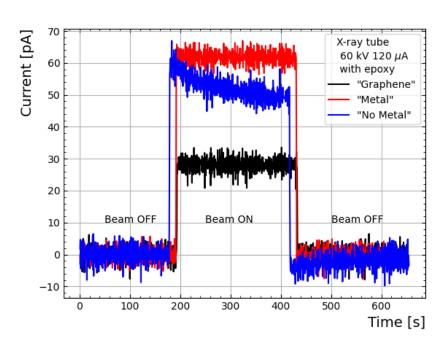
Devices: SiC-Graphene

SiC-Metal

SiC-No Metal

Readout: Sun Nuclear e-meter







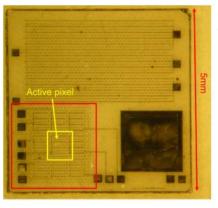




All-carbon diamond detector approach

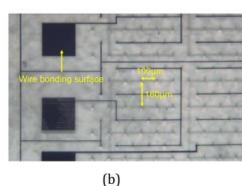
Typically fabricated with laser graphitisation, replacing metal by other groups

 Slow for large production! => O(10um/s) laser movement



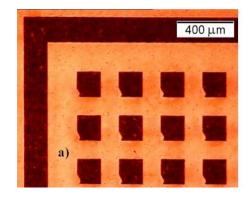
(a)

Diam and Rel Mat 133 109692 (2023)



Next is an attempt to produce All-carbon devices with a different approach (available in the CNM clean room)

NIMA 837 136142 (2016)



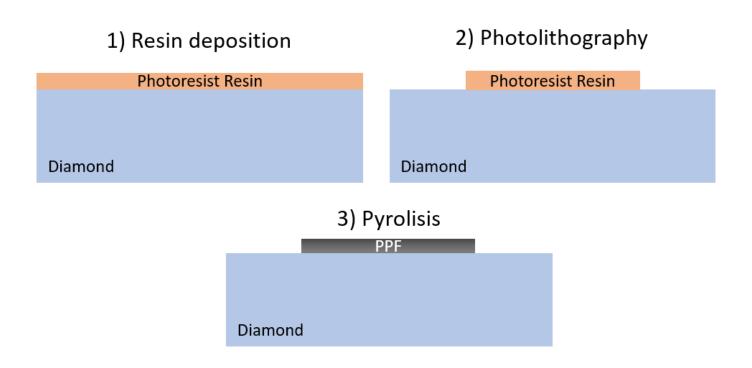




First proof-of-concept via PPF: Fabrication

Pyrolitic Photoresist Film:

 Sublimate non-carbon components from resin with high temperature

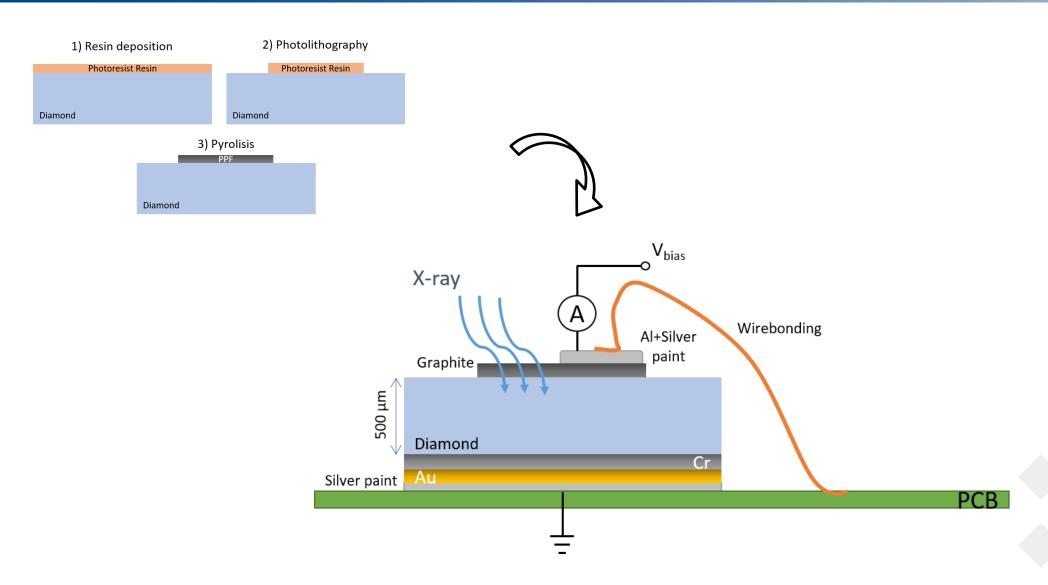


Simple technological process, easy to scale for production!





First proof-of-concept via PPF: Fabrication



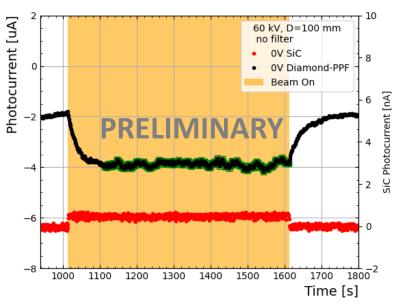


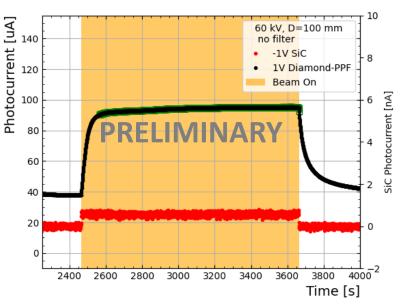


First proof-of-concept via PPF: Characterisation with X-ray tube

Measure photocurrent, with beam on for 5 min at different beam currents:

- Prototype is responsive even at 0V!
- It's slow, needs about 100 sec to stabilise due to bulk material quality
- Needs pre-irradiation / "priming", usual case for diamond in general







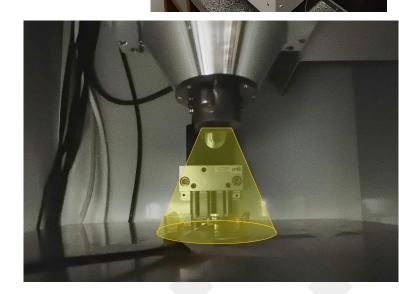
Op. Voltage: 60kV

Beam current: 60-120 uA

Devices: Diamond-PPF

SiC diode

Readout: Keithley 2410



NOTOCAR

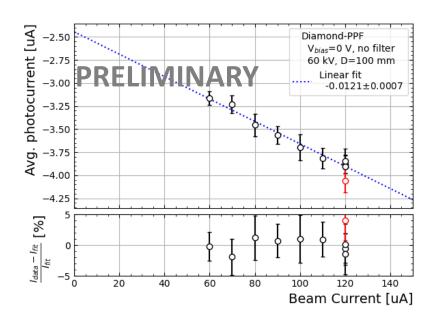


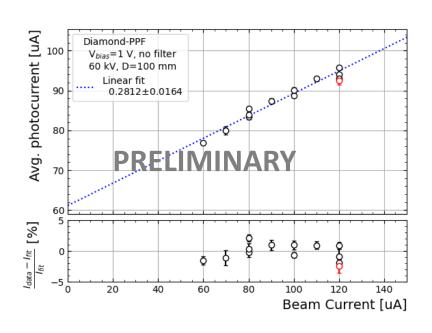


First proof-of-concept via PPF: Characterisation with X-ray tube

Measure photocurrent, with beam on for 5 min at different beam currents:

- Prototype is responsive even at 0V!
- It's slow, needs about 100 sec to stabilise due to bulk material quality
- Needs pre-irradiation / "priming", usual case for diamond in general





Tungsten anode X-ray tube

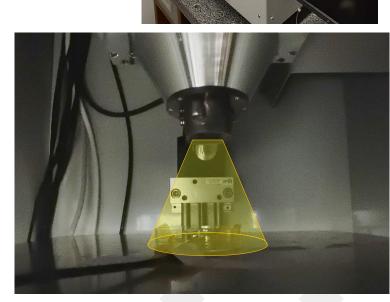
Op. Voltage: 60kV

Beam current: 60-120 uA

Devices: Diamond-PPF

SiC diode

Readout: Keithley 2410



NOTOCAR

Wide band-gap detectors for dosimetry fabricated at IMB-CNM:

Silicon Carbide diodes with Graphene:

- Graphene improves charge collection on SiC diodes over not having metal
- Prototype works with good linearity in LINAC and laboratory

Diamond with PPF graphite:

- Proof-of-concept tested in laboratory
- Sensitive to lab X-rays

Next:

- Need to improve packaging
- Test under FLASH conditions
- Irradiations/radiation resistance





Thanks for your attention

C/ del Til·lers s/n Campus de la Universitat Autònoma de Barcelona (UAB) 08193 Cerdanyola del Vallès (Bellaterra) Barcelona · Spain



www.imb-cnm.csic.es

Back-up slides

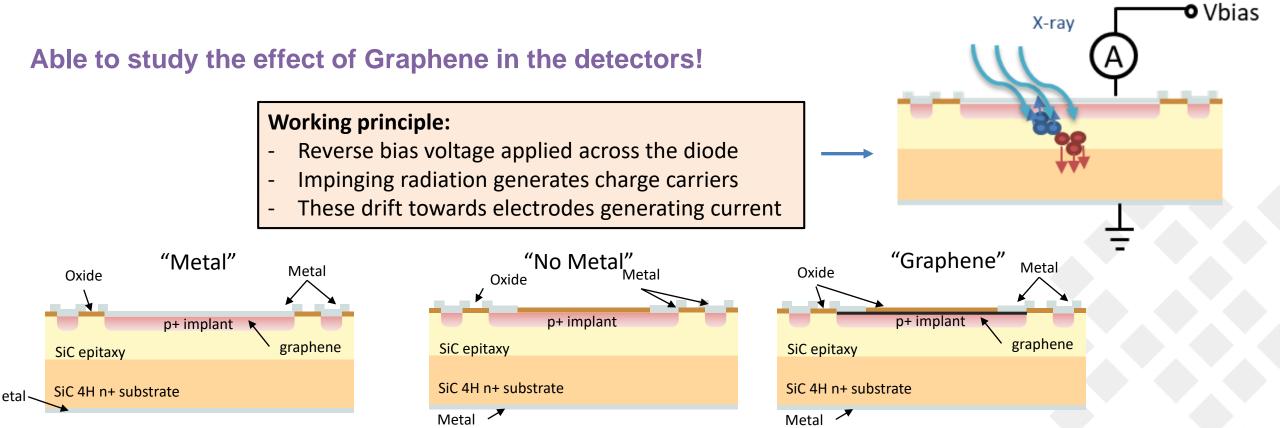




SiC detectors with Graphene contacts

SiC diodes (50um epitaxy) with three geometries fabricated at CNM

- Metal: Metallic contact over all active region
- No Metal: Metal ring around the active region, nothing elsewhere
- Graphene: Graphene layer contact over all active region, with metal ring for wirebonding
- Front (Ti 20nm/Pt 100nm/Au 100nm) and back (Ti 50 nm /Ni 150 nm /Au 50 nm) metals for contact





Contact resistance and contact resistivity

- Measured by CTLM in test structures
- Irradiation campaigns at the ATI Triga Mark
 II nuclear reactor
- R_{sh} : related to doping concentration
 - Increase as a function of fluence
 - Indication of acceptor removal
 - Consistent across EG-SiC and SiC samples
- ρ_c : related to metal-(graphene)-SiC contact
 - Increase as a function of fluence
 - EG-SiC sample much higher resistivity
 - Effect of graphene interface
 - Difference between SiC samples
 - Different metal stacks

100	
Device	Metallisation
SiC Chip1	Ti/Al/Ti/W
	(15/90/30/100 nm - evaporation)
SiC Chip 2	Ti/Pt/Au
	(20/100/100 nm - sputtering)
EG-SiC Chip8	Ti/Pt/Au (20/100/100 nm - sputtering)

Mean sheet resistance vs. fluence SiC Chip 1 SiC Chip 2 100 100 EG-SiC Chip 8 80 $\mathsf{R}_{\mathrm{sh}}\left[\mathrm{k}\Omega\right]$ 60 60 20 10¹⁴ 10¹⁵ 10¹⁶ 0.00 (a) fluence [cm⁻²] Mean contact resistivity vs. fluence 10⁰ 10⁻¹ 10⁻¹ $ho_{ m c} \left[\Omega { m cm}^2 ight]$ 10-2 10⁻³ 10⁻³ SiC Chip 1 SiC Chip 2 EG-SiC Chip 8 10^{-4} 0.00 (b) fluence $[\mathrm{cm}^{-2}]$

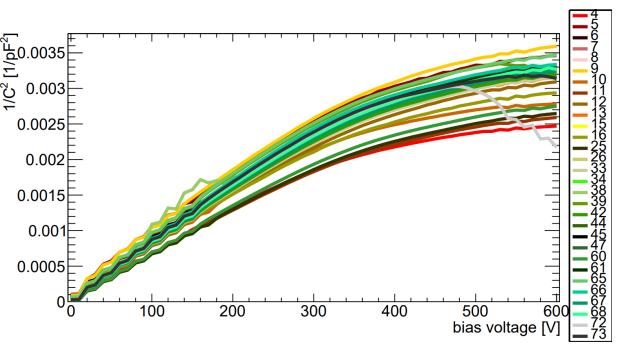
S. Otero Ugobono et al, Materials Science Forum. Trans Tech Publications, Ltd., May 31, 2022



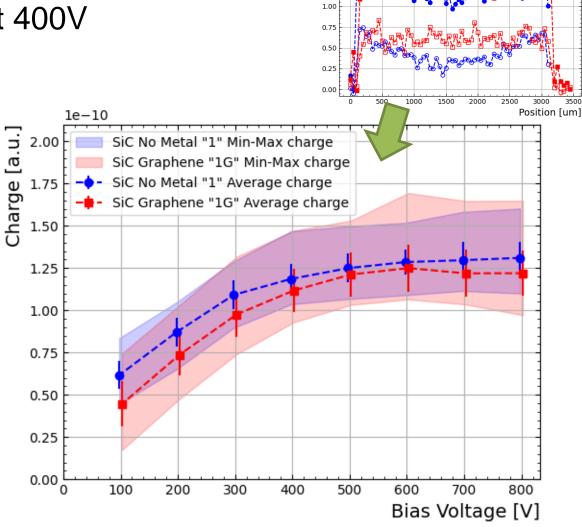


Charge collection vs Voltage

- Both samples seem to start to saturate at 400V
- Consistent with C-V measurements



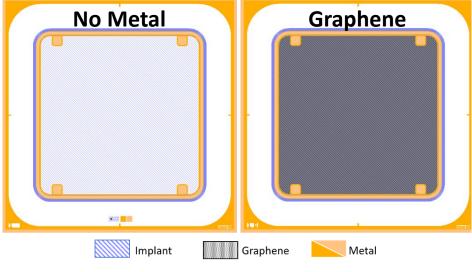
Presence of graphene does not affect saturation voltage

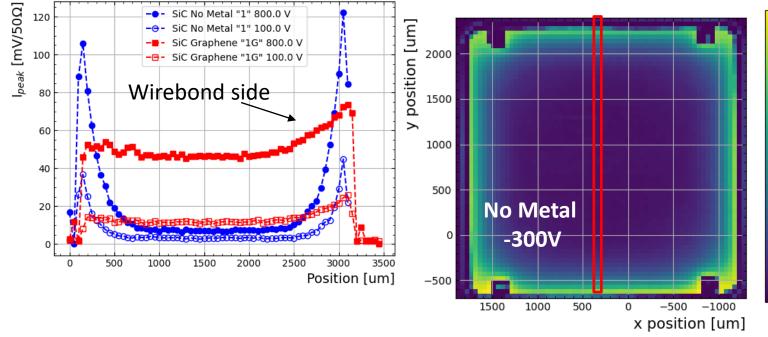


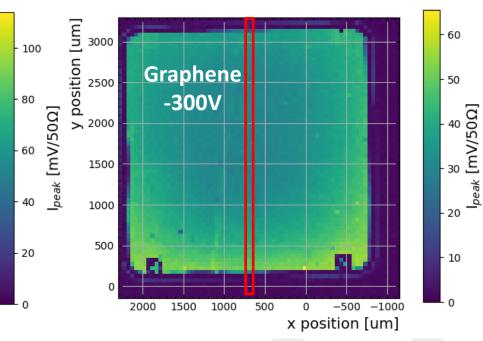




The **amplitude of the signals** are higher over most of the active region in the "Graphene" sample...









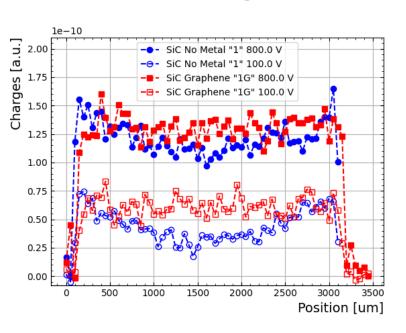


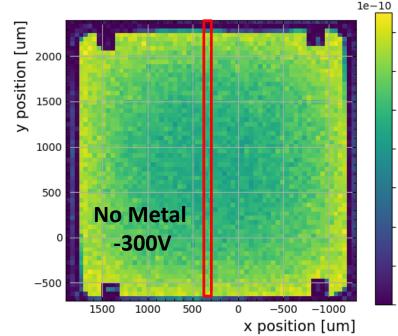
No Metal

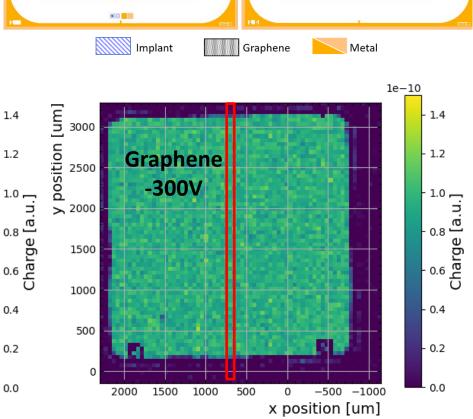
The **amplitude of the signals** are higher over most of the active region in the "Graphene" sample

And uniform **charge collection** across samples provided large enough integration window in "No Metal" sample (more sensitive to noise).

Graphene helps in making signals more uniform across the device over charge collection across implant (no metal)





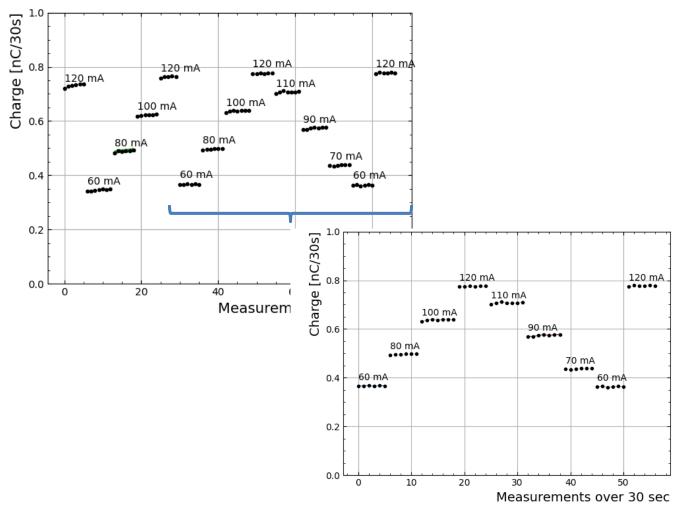


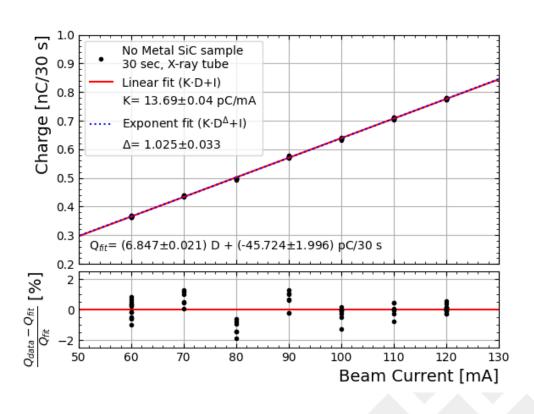
Graphene





"No Metal" X-ray tube results





"No Metal" sample seems to struggle with linearity and stability

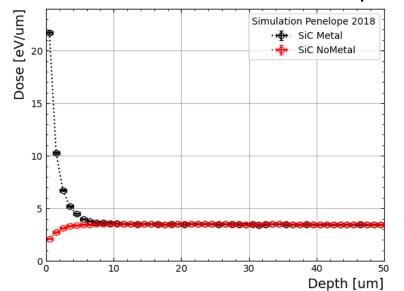


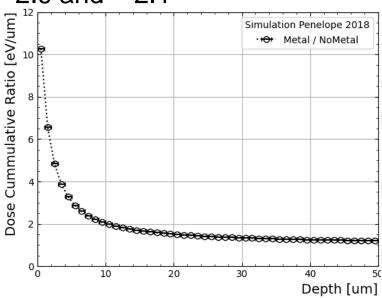
X-ray tube results

Simulation with Penelope 2018

- 1.2 mm Al, 10mm PMMA, Metal stack (when applicable), 50um+250 um SiC,
 Metal stack (Graphene is negligible)
- Results:
 - Dose in the first 5 um in the saple with metal contact is several times higher than that without metal, then othey are the same

Considering that 0V depletion distance is ~5-10 um (see TPA-TCT slides in RD50 Seville),
 the ratio of accumulated dose across that depth ranges between ~2.9 and ~ 2.1









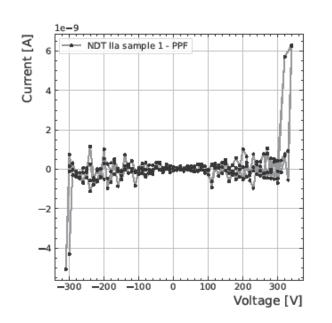
First proof-of-concept via PPF: Fabrication

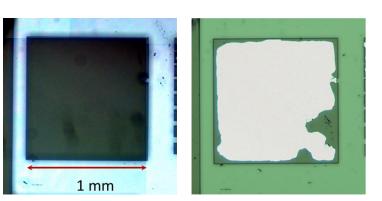
Pyrolitic Photoresist Film:

 Sublimate non-carbon components from resin with high temperatura

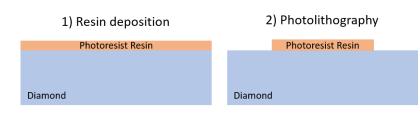
HPHT Type IIa diamond to produce proof-of-concept

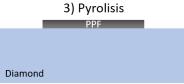
For wirebond connection add Al layer





Good electrical behaviour before packaging











First proof-of-concept via PPF: Fabrication

Pyrolitic Photoresist Film:

 Sublimate non-carbon components from resin with high temperature

HPHT Type IIa diamond to produce proof-of-concept

For wirebond connection add Al layer

Silver paint to aid wirebond (low adhesión)

... since then leakage current @ > 0 V very high, but works

First prototype fabricated!

Al+Silver paint

Diamond

Silver paint

PCB

